

# Key Methods in Reducing Pad Crack Risk at Probing Low-k Wafers



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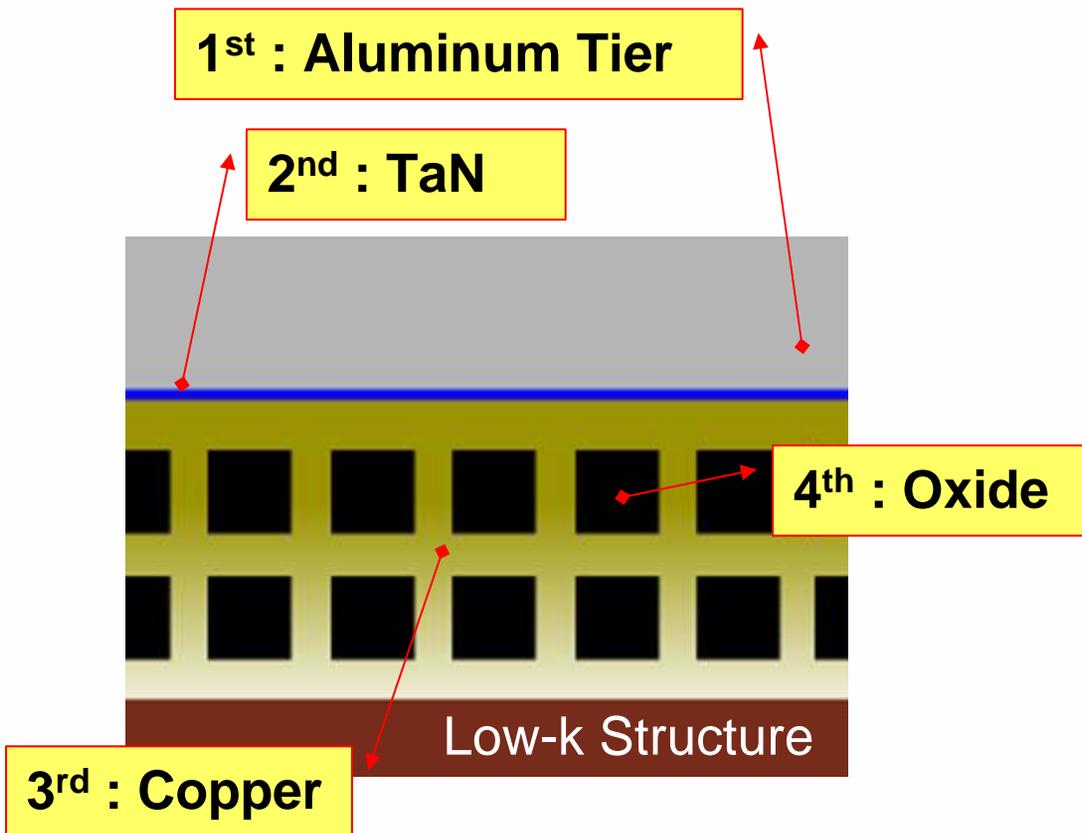
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# Agenda

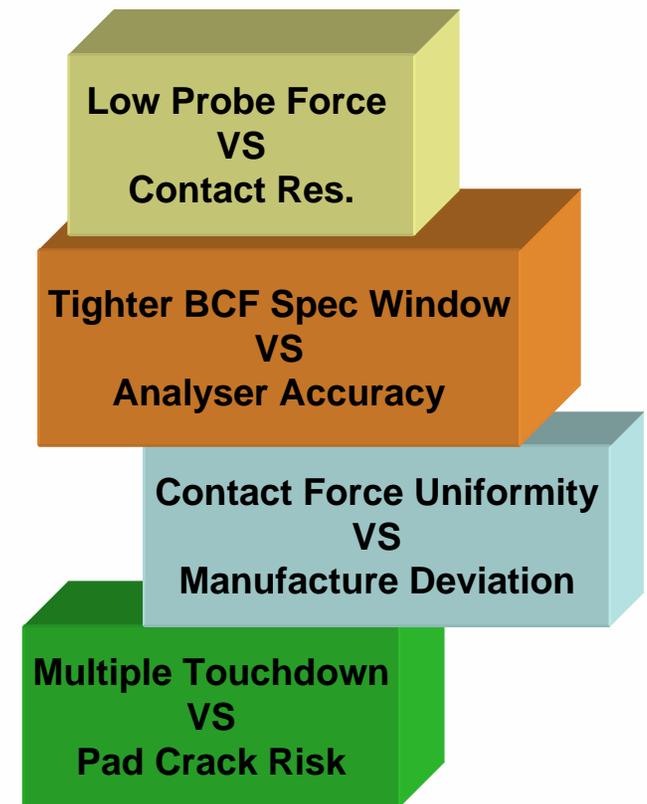
- **Probing Challenge on Low-k Devices**
- **Scrub Depth Correlates with Underneath Layers**
- **Scrub Depth Model Formulation (SDMF)**
  - Review -2005
  - Experiment and Result
  - Constant Parameter Calculation
- **BCF Measurement Limitation**
- **Conclusion**

# Probing Challenge on Low-k Devices



Low-k experimental wafer – Pad matrix cross section

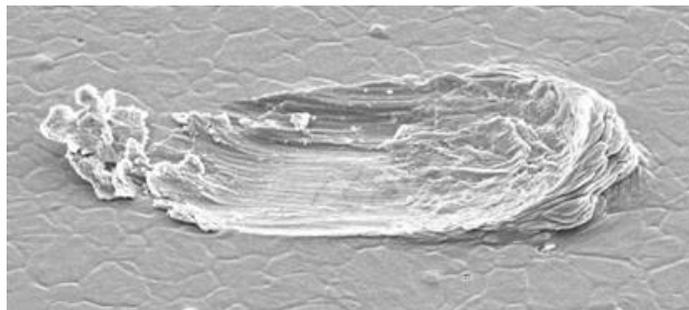
## Probing contradictory!



# Probing Challenge on Low-k Devices

## What Should Be Concerned on Low-k?

- Except Pad Void (PV), what risks will be suffered when probing Low-k wafer?
- In comparison with the low-k defects, It's "lucky" to suffer PV, because of the observable defects where after aluminium layer removal, copper is physically exposed on TaN surface.
- How about the scrub below?  
It's OK or NG? In fact, microscope and wafer inspector show you "No PV."

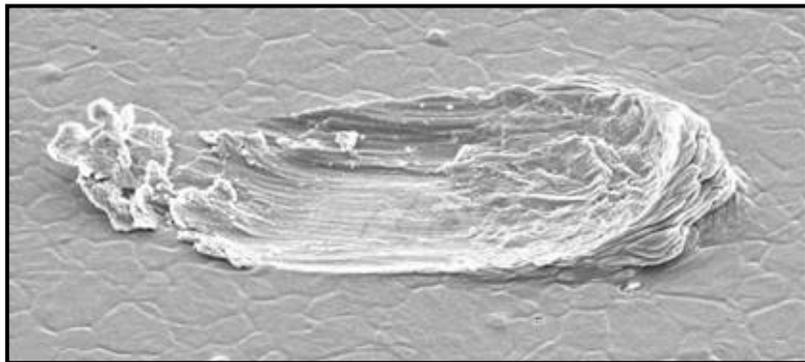


Al Remove

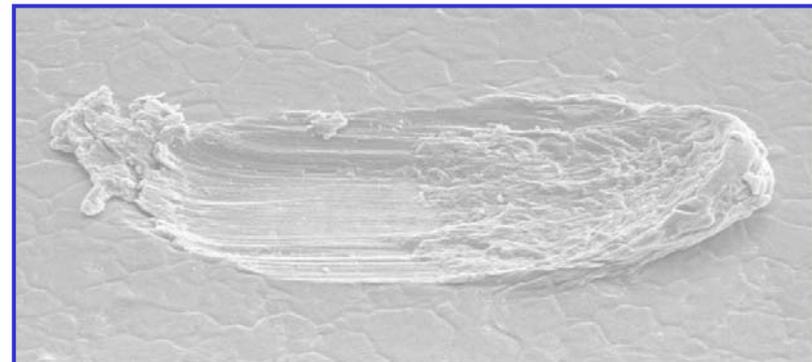
# Probing Challenge on Low-k Devices

## Hidden Underneath Layer Deformation

- No PV  $\neq$  Free Damage



BCF:4gw/mil Tip Dia.=8um  
OD= 45  $\mu$  m Probe:6 times

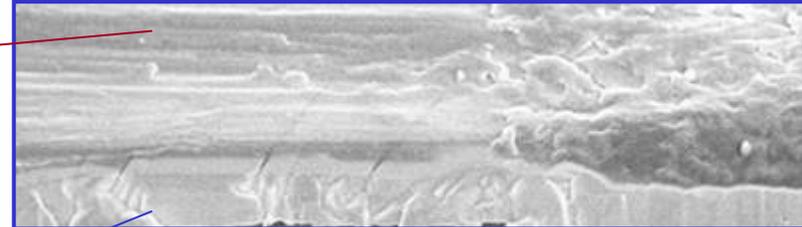


BCF:4gw/mil Tip Dia.=14um  
OD=45  $\mu$  m Probe:6 times

Cross  
Section



Deformation



Serious Destruction

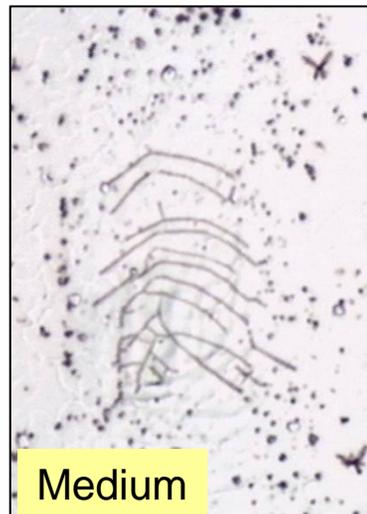
Cu

Al

# Probing Challenge on Low-k Devices

## Initial Probing Damage

- After Al was removed, we found micro scratches and cracks as below images:



OD= 65  $\mu$ m  
TD=6 times  
Tip Dia.=8  $\mu$ m  
BCF=4gw/mil



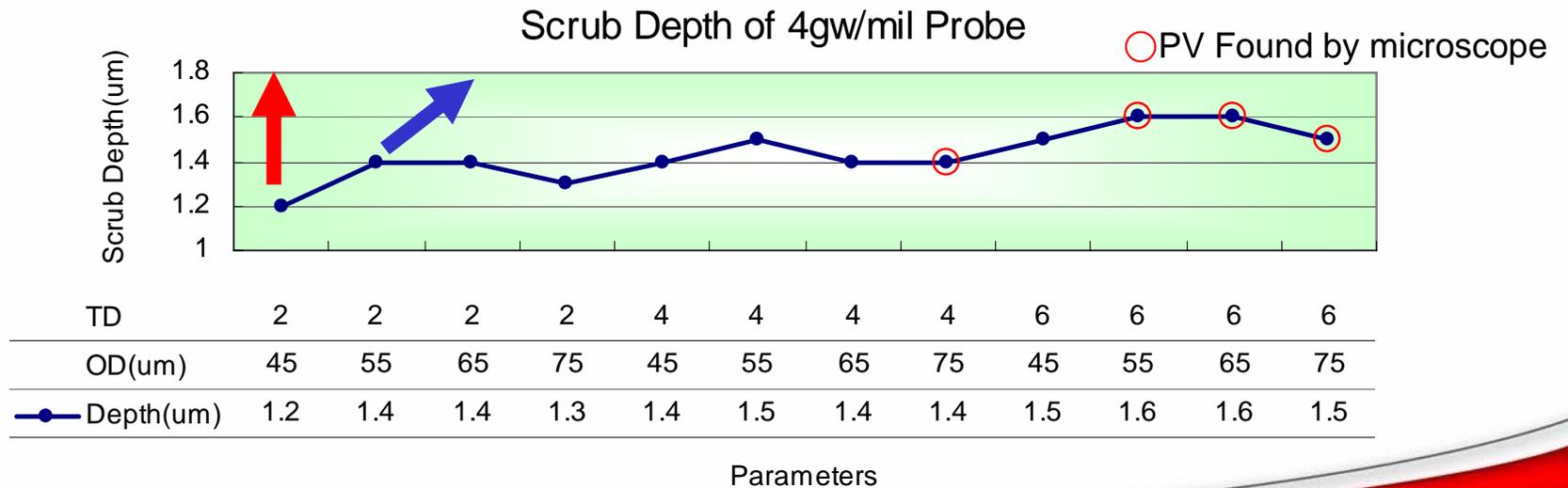
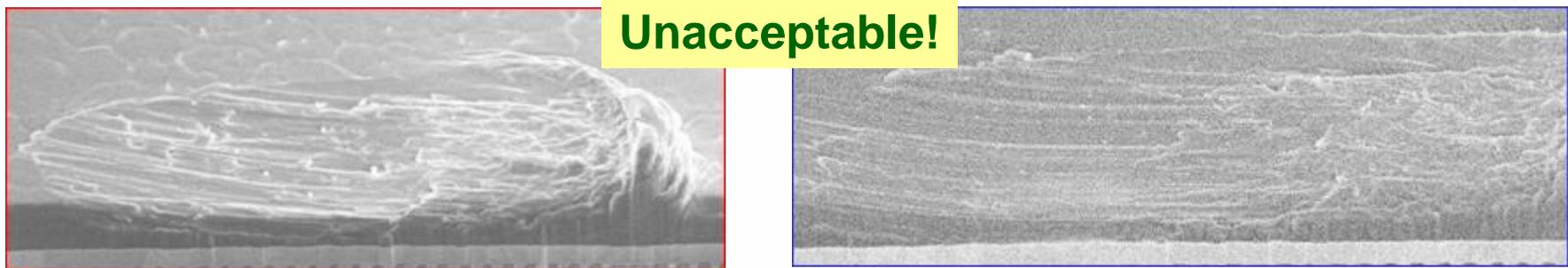
Scrub  
direction

- Evaluation showed the probability of probing damage:  
TaN Crack > Underlying Deformation > Pad Void
- Safe probing method is to prevent TaN-crack!

# Scrub Depth Correlates with Underneath layers

## Underneath Layer Evaluations

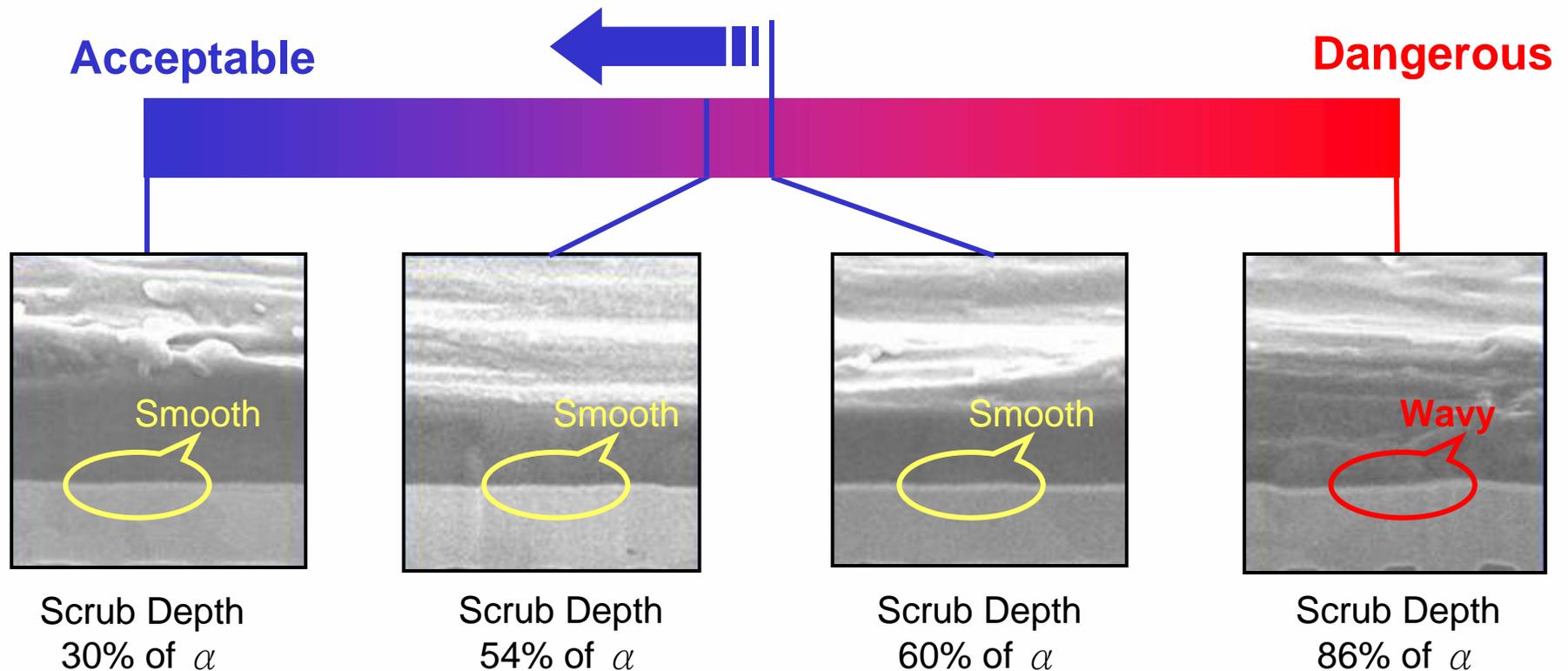
- Measurements identified underneath layer deformation risk was at stake.



# Scrub Depth Correlates with Underneath layers

## Acceptable Scrub Depth Region

- Monitor the TaN layers of shallow scrubs.



$\alpha$  = Thickness of Al Layer

# Scrub Depth Correlates with Underneath layers

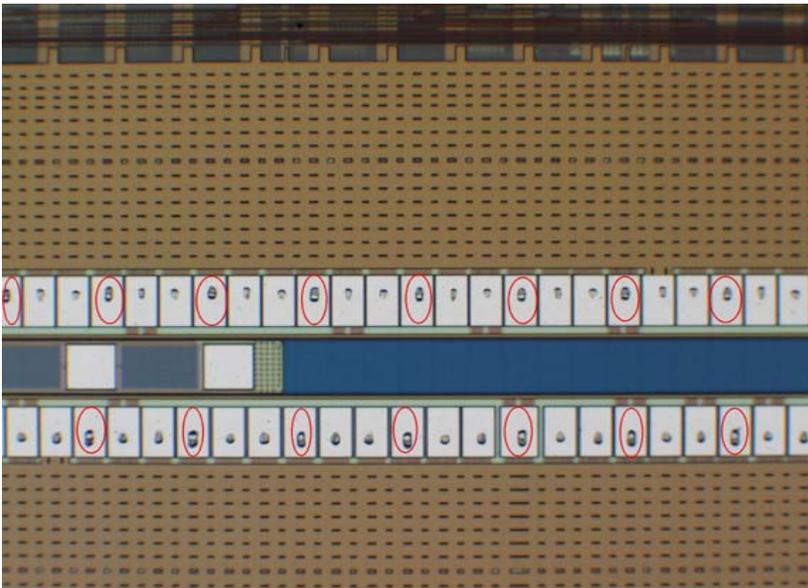
## Scrub Depth Control is Necessary

- ❑ Low-k devices are highly sensitive to probing force issue, more severely is the unobservable physical damage inside the pad.
- ❑ Hidden damage not seen at wafer inspect after probing, but identified at test failure during packaging/final test.
- ❑ Experiment and evaluation works indicated the safety band probing depth region is fallen below 60% of total Al thick.
- ❑ Efficient methodology to control the scrub depth is proposed by monitoring the Kyy as the primary dominant factor.
- ❑ Continuing the last year presentation on SWTW 2005, the proposed SDMF will be demonstrated again as an effective backend assessment methodology to prevent the probing damage.

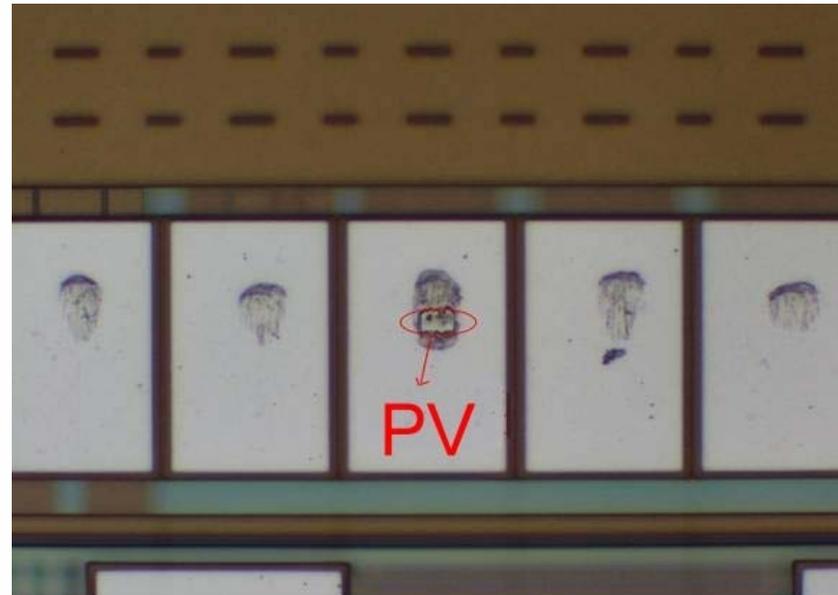
# Scrub Depth Model Formulation (SDMF) PV Case in TSMC

2005 SWTW

- Problem description
  - Pad void by 1<sup>st</sup> layer needle



Repeated PV patterns



# Scrub Depth Model Formulation (SDMF)

## Primary Factors of Experiment I & II

- By choosing all critical parameters, a two-level L8 orthogonal array experiment I has been performed, the influential factors have been determined as follow:
  - Primary dominant factors → **tip length, tip diameter**
  - Secondary dominant factors → stiffness  $K_{yy}$ , needle diameter
- From TSMC mass production testing, three critical parameters were chosen to perform experiment II with a L9 three-level setting. The summarized results are:
  - Primary dominant factors → **tip length, stiffness  $K_{yy}$**
  - Secondary dominant factors → tip diameter
- The slight variation in results of these two experiments, it was recognized that these experiments still had uncontrolled noise.
- It is concluded that these two experiments indicated that **tip length, tip diameter, stiffness  $K_{yy}$**  were the three most influential primary parameters.

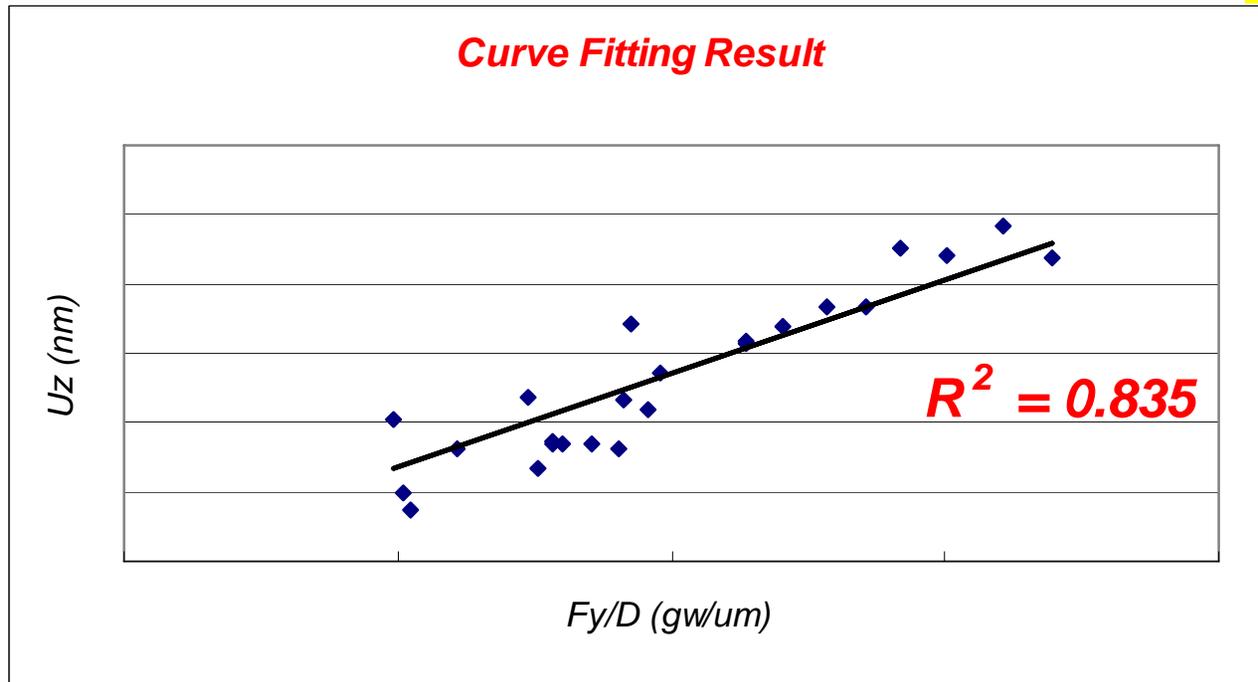
# Scrub Depth Model Formulation (SDMF)

Theory, Experiment and Verification

2005 SWTW

- Constant values B & C were found from curve fitting.

$$\begin{aligned}\bar{U}_z &= C \frac{F_y}{D} \\ &= C (BK_{yx} + K_{yy}) \frac{D_y}{D}\end{aligned}$$



Unit :

$\bar{U}_z$  : nm

$K_{yx}, K_{yy}$  : gw/mil

$D_y$  : mil

$D$  :  $\mu\text{m}$

# Scrub Depth Model Formulation (SDMF)

Theory II , Experiment II , and Verification II

- Experiment background
  - Applicability of the model is evaluated.
  - Two more parameters included:
    - (1) Three most commonly used prober machines
    - (2) Different needle diameter (4 mils)
  - Prober set-up based on TSMC production used methods.

- Results

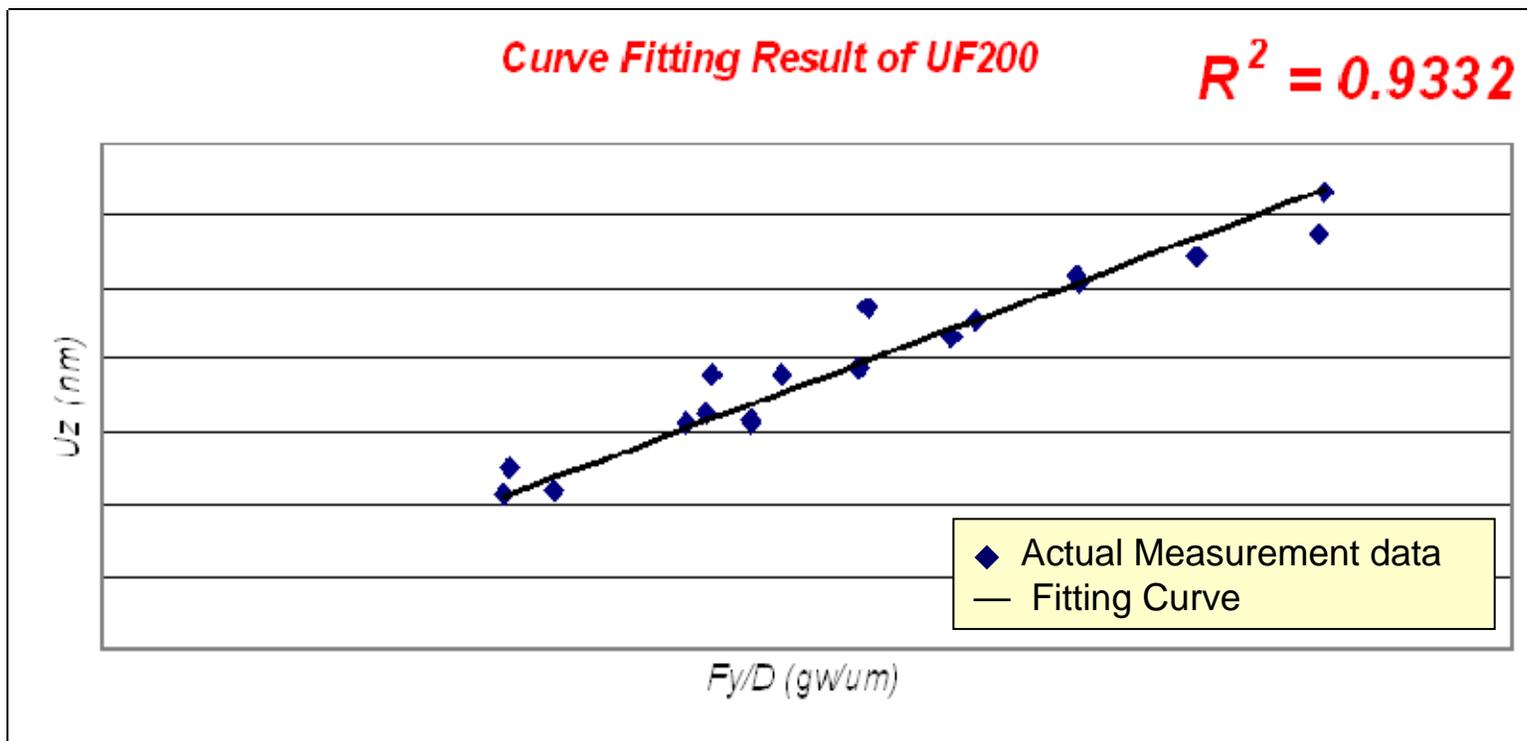
Prober		Probe			
Type	OD ( $\mu$ m)	Tip Dia. ( $\mu$ m)	Tier	Stiffness-Kyx (gw/mil)	Stiffness-Kyy (gw/mil)
<b>UF200</b>	40	8 13	1-3	1st: 7.28	2
<b>UF3000</b>	60			2nd: 5.23	
<b>TEL P12</b>	75			3rd: 4.19	

Additional set up notes:.. undershoot at UF prober is 25  $\mu$ m, while on TEL P12, double touchdown function is activated.

# Scrub Depth Model Formulation (SDMF)

Theory II , Experiment II , and Verification II

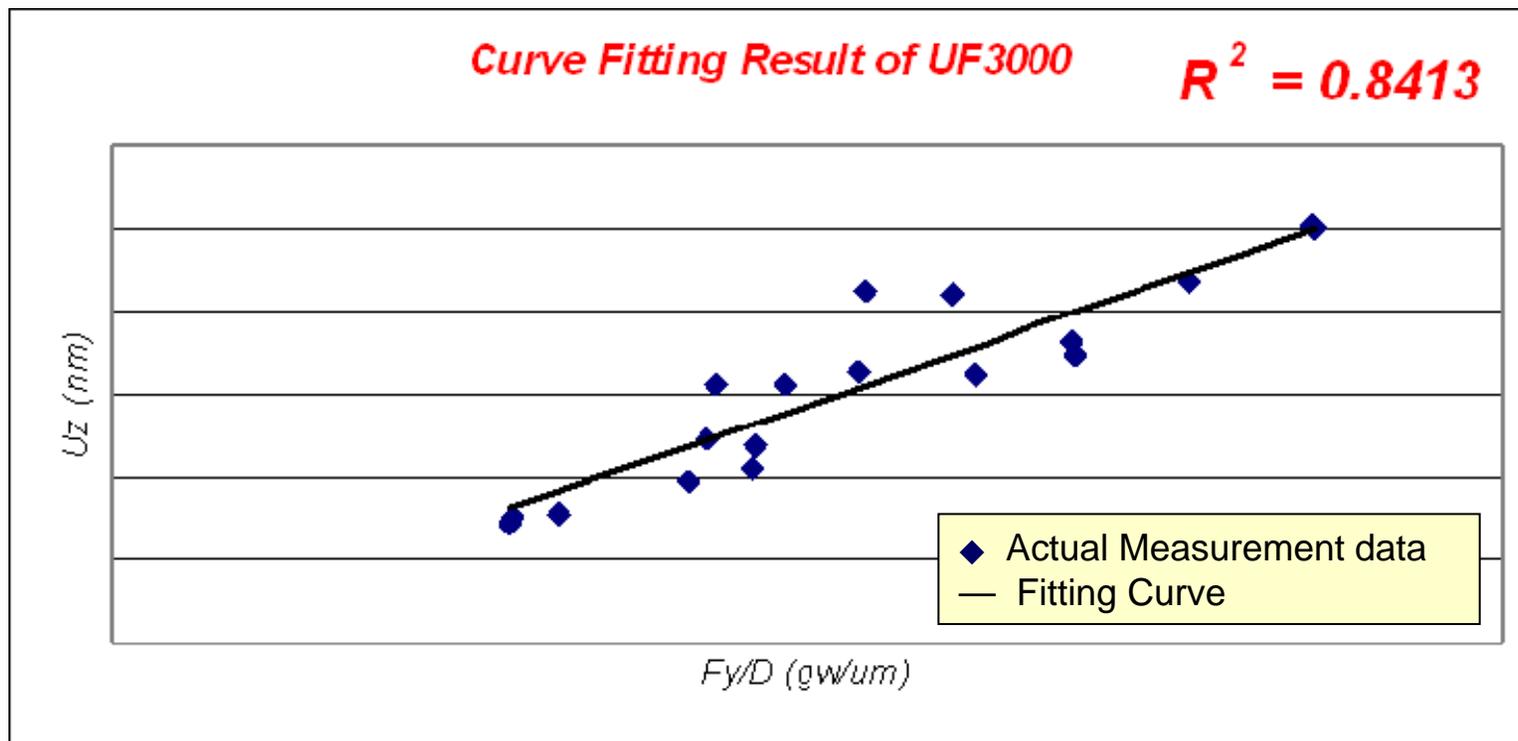
- R-square was in high agreement for UF200



# Scrub Depth Model Formulation (SDMF)

Theory II , Experiment II , and Verification II

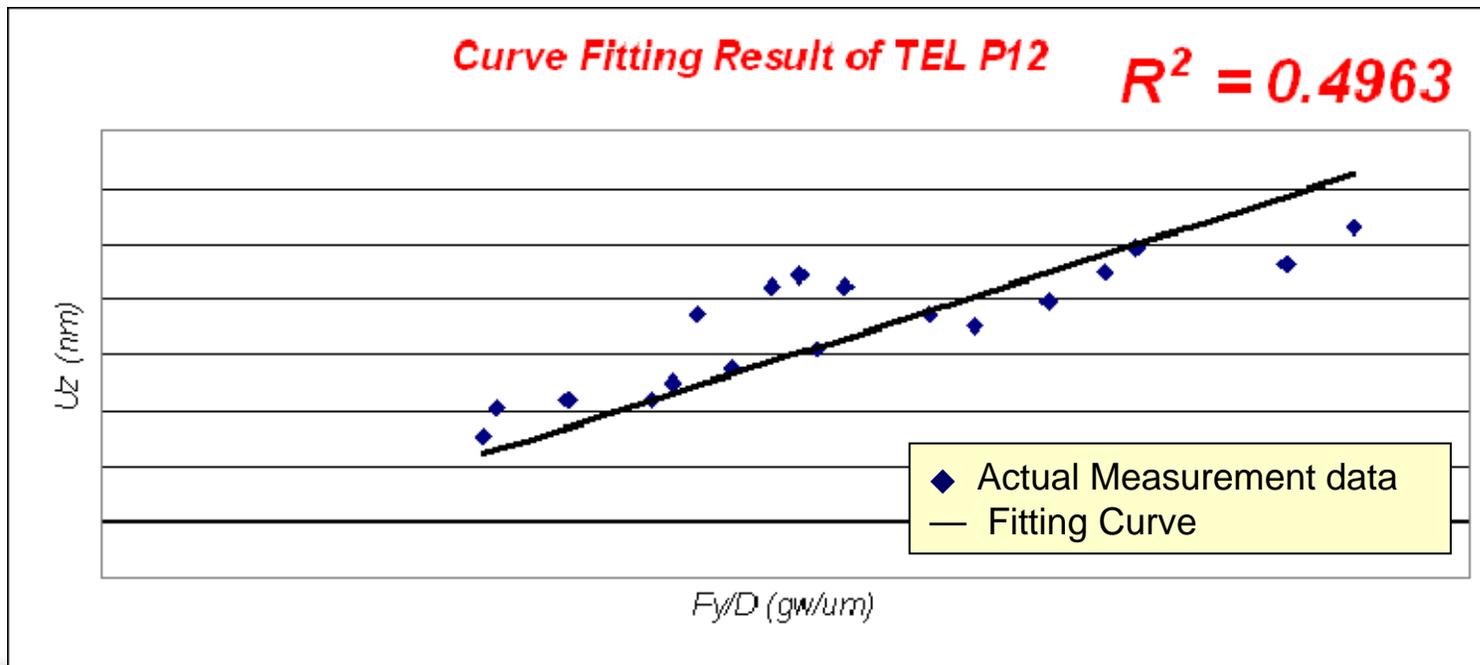
- **UF3000** also showed appreciable agreement



# Scrub Depth Model Formulation (SDMF)

Theory II , Experiment II , and Verification II

- R-square showed lower fitting agreements.
- Prober chuck movement mechanism was attributed as major factor in the result variation.
- Initial guess is TEL P12 having deeper probing height than UF families.

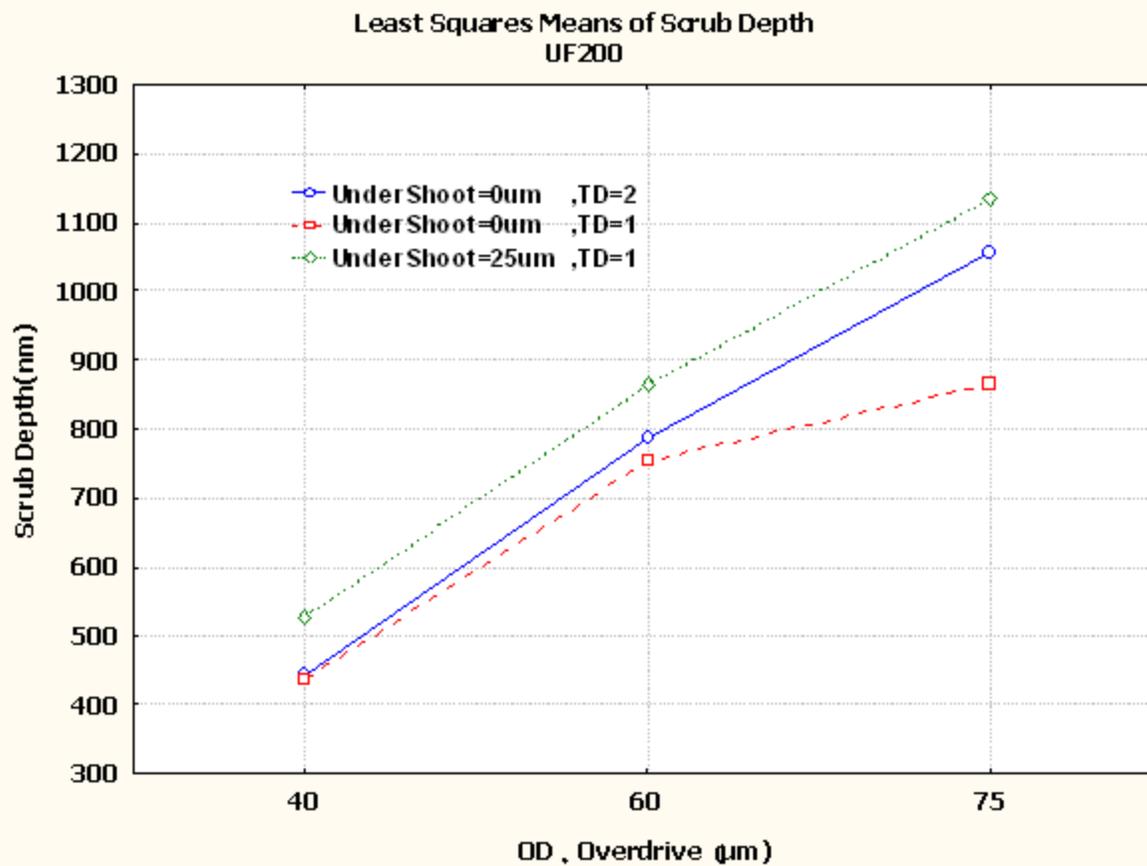


# Scrub Depth Model Formulation (SDMF)

Theory II, Experiment II, and Verification II

- **SDMF – Constant parameter calculation**

【UF200】



Two normal TDs scrubbed 2~22% deeper than single TD. (see blue vs. red line)

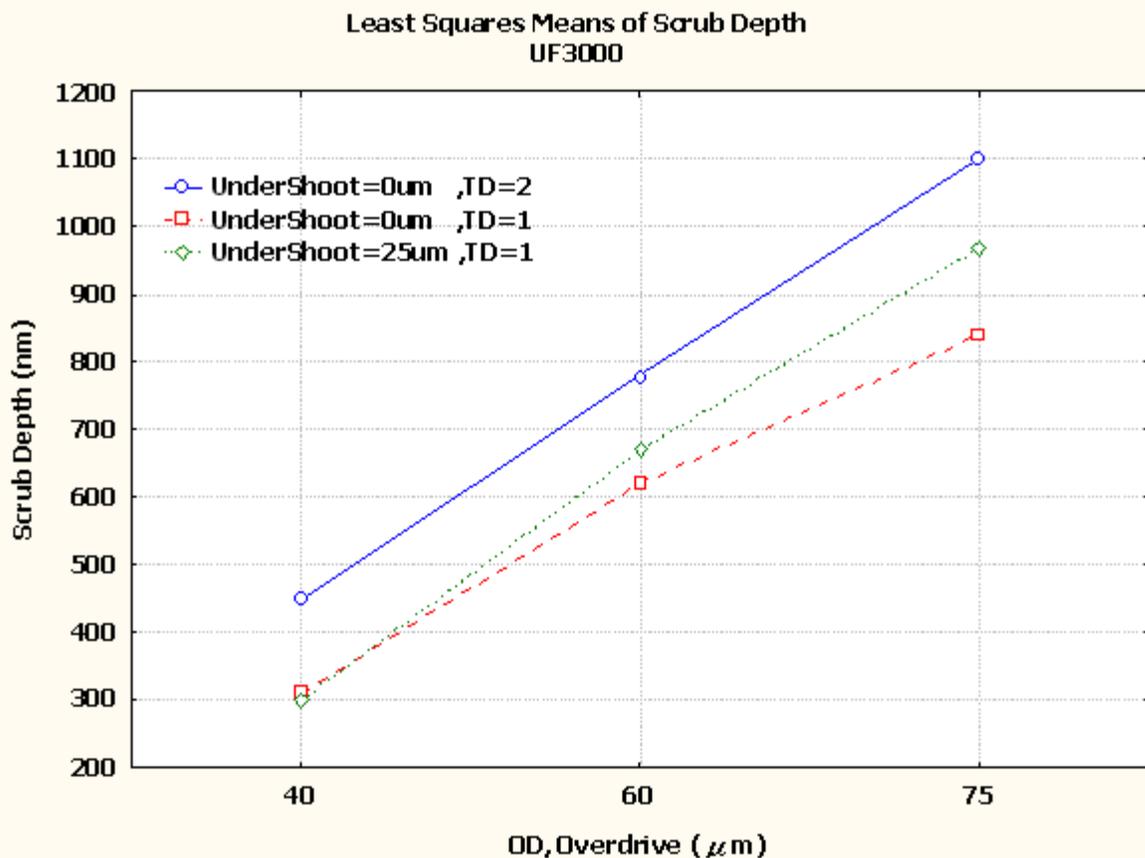
25um undershoot TDs has 15~30% deeper scrub mark than the non-undershooting one. (see green vs. red line)

# Scrub Depth Model Formulation (SDMF)

Theory II, Experiment II, and Verification II

## ● SDMF – Constant parameter calculation

【UF3000】



Two common TDs generated 25~45% deeper scrub than with only 1 TD. (see blue vs. red lines)

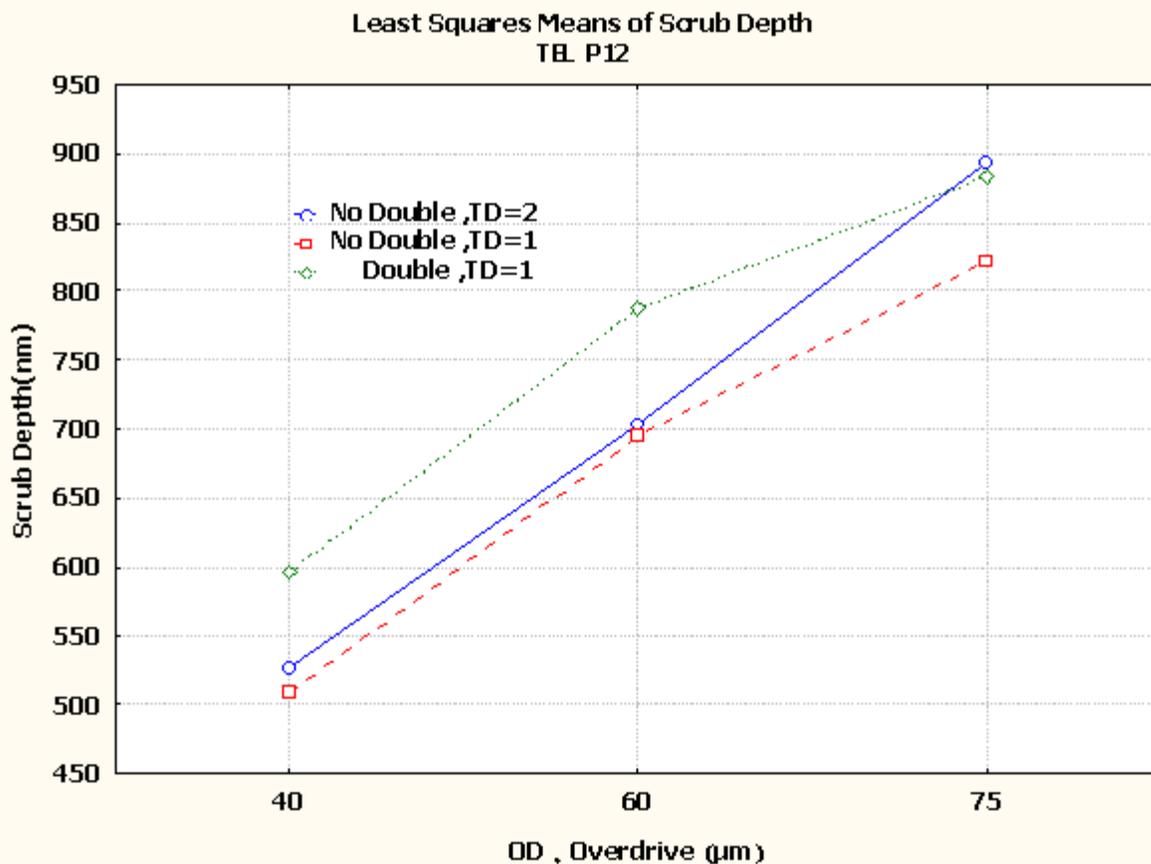
Activating undershoot 25um, scrubs became 0~15% deeper than non activated one. (see green vs. red lines)

# Scrub Depth Model Formulation (SDMF)

Theory II, Experiment II, and Verification II

## ● SDMF – Constant parameter calculation

【TEL P12】



“TEL double touchdown” function physically differs with UF’s “undershoot function.”

Two normal TDs’ scrub marks were 4~9% deeper than the one by single TD.  
(blue vs. red)

After activating “double touchdown”, scrub is increasingly 8~17% deeper than non-activated one.  
(green vs. red)

# Scrub Depth Model Formulation (SDMF)

## Summary

- ❑ SDMF results again showed the high level of quantitative prediction agreement with the corresponding experimental measurement data.
- ❑ “Linear Scrubbing / Slope Scrubbing” based assumption of SDMF is theoretically and experimentally proven to be capable of predicting the scrub depth the complex scrubbing action.
- ❑ Constant parameter modification factors of prober including set-up and multiple TDs functions, still need further statistic sampling data to obtain accurate results.
- ❑ Measurement errors existed in the experimental data is still acceptably tolerable as to be used in engineering level application.
- ❑ Production data feedback is always an on-going process for better modification results of certain constant values of the model.

# BCF Measurement Limitation

Analyzer, Statistic, Experiment

- BCF control is unavoidable for low-k probing
- How to address a common BCF definition by suppliers and vendors ?
- Currently the industry available BCF measurement tooling (ex. Equipment A) showed spec as below :

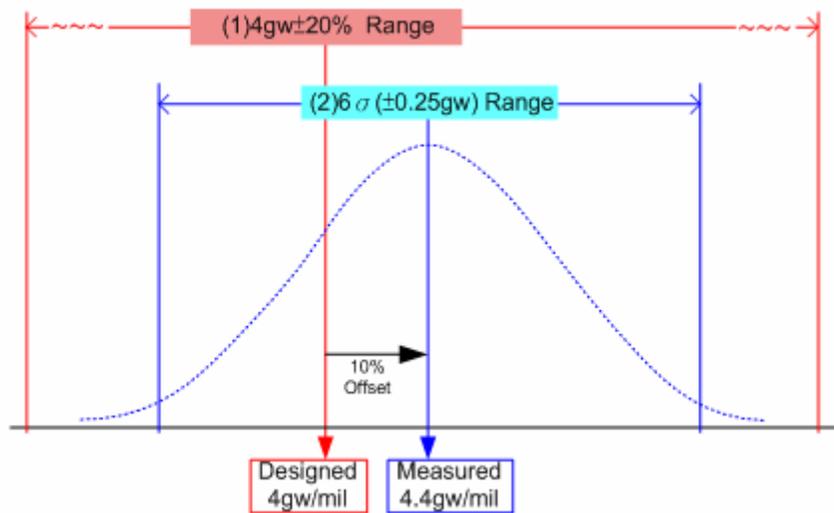
Probe Force & Z-Force	Travel	Load	Repeatability	Accuracy
Probe Force shown @ $3\sigma$	0-30 grams	Max Load: 50	$\pm 0.12$ grams	$\pm 0.25$ grams
Maximum Z-Force		130 lbs. (60 kgs)		

Simply states:

With measured value 1gw/mil, it will have confidence intervals 99.7% that the deviation range should fall from 0.75~1.25 gw, also denoted as  $(1\text{gw} \pm 25\%)$

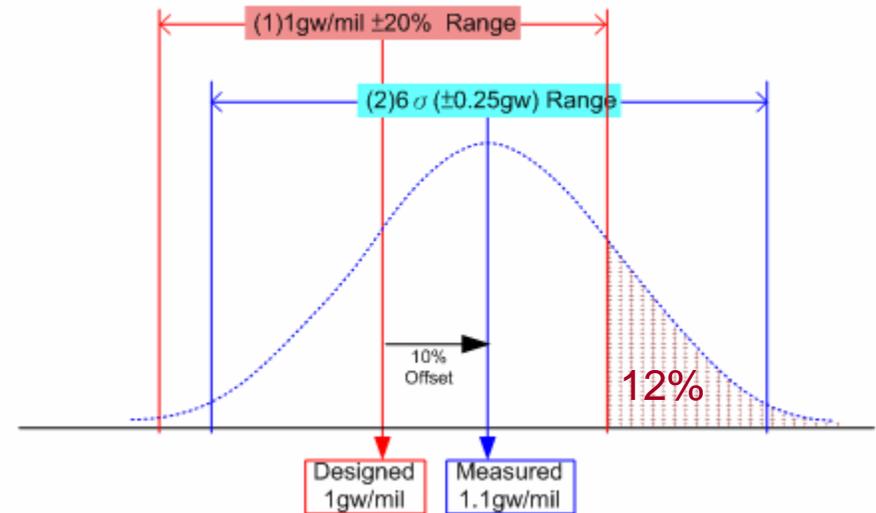
# BCF Measurement Limitation

Analyzer, Statistic, Experiment



- (1) BCF Spec: 4gw/mil ± 20%
- (2) Accuracy: ±0.25gw @ 3σ

10%-offset BCF Measure  
100% confidence within Spec.



- (1) BCF Spec: 1gw/mil ± 20%
- (2) Accuracy: ±0.25gw @ 3σ

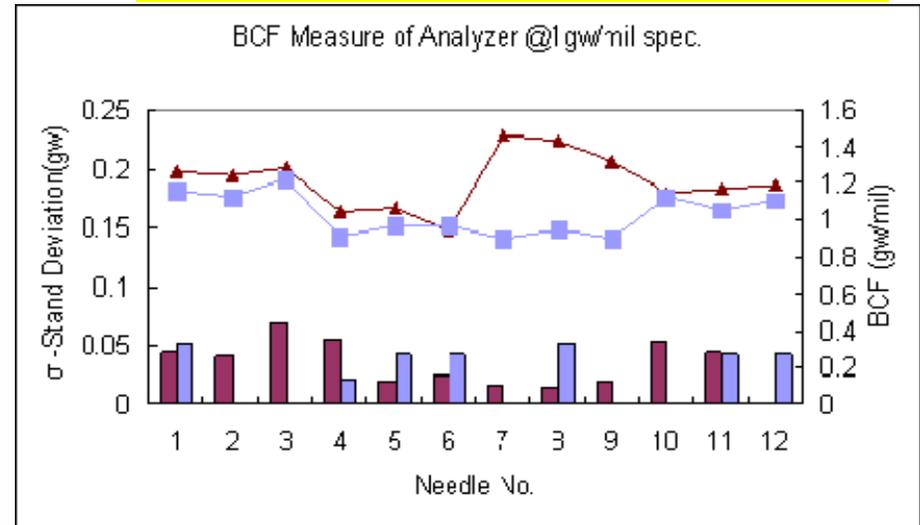
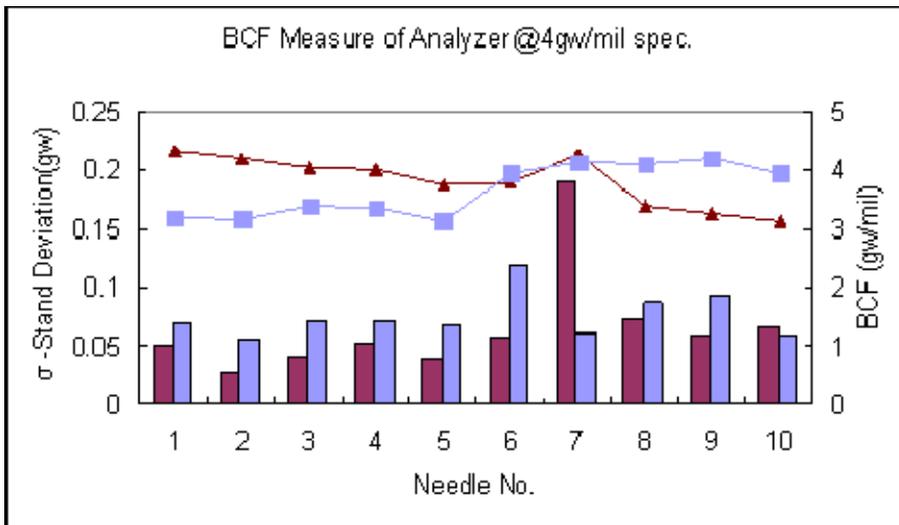
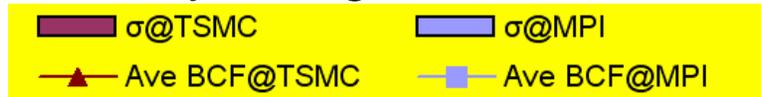
10%-offset BCF Measure  
88% confidence within Spec.

As metrology accuracy has been pushed to its limit, allowable manufacture deviation suffers more and more tighter tolerance. New BCF metrology platform is urgently needed.

# BCF Measurement Limitation

## Analyzer, Statistic, Experiment I

- At low BCF values, measurement accuracy is degraded to marginal range



Average Standard Deviation:

$\sigma_{Ave}$ -TSMC is 0.065

$\sigma_{Ave}$ -MPI is 0.075

BCF under  $3\sigma$  confidence interval:

TSMC  $\doteq \mu \pm 0.195$       4 gw/mil  $\pm 5\%$

MPI  $\doteq \mu \pm 0.225$       4 gw/mil  $\pm 5\%$

Average Standard Deviation:

$\sigma_{Ave}$ -TSMC is 0.033

$\sigma_{Ave}$ -MPI is 0.025

BCF under  $3\sigma$  confidence interval:

TSMC  $\doteq \mu \pm 0.1$

MPI  $\doteq \mu \pm 0.075$

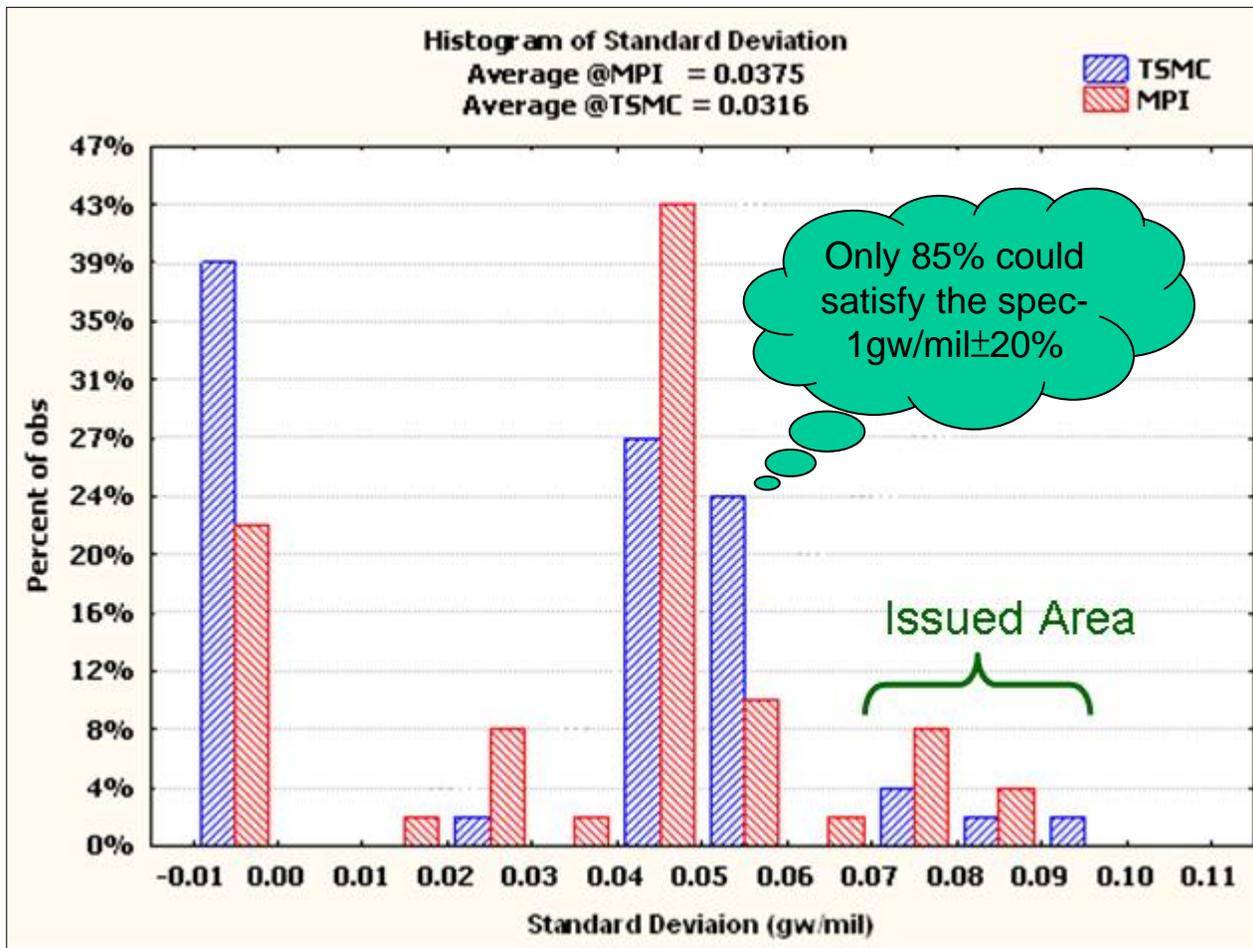
**Accuracy is getting worse !**

1 gw/mil  $\pm 10\%$

1 gw/mil  $\pm 7.5\%$

# BCF Measurement Limitation

Analyzer, Statistic, [Experiment II](#)



Procure a qualified low-k probe card.

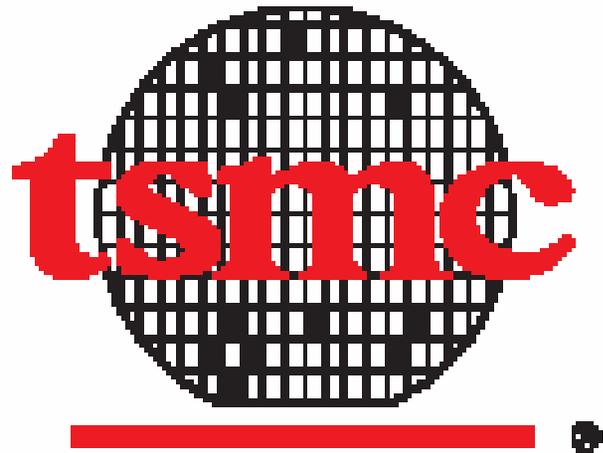
Carried out 5 repetitive BCF measurements from selected 50 pins.

For required spec  $1\text{gw/mil} \pm 20\%$ , sigma must at  $< 0.07$  for obtaining less debatable data

More sampling data for meaningful statistics.

# Conclusion

- High density of mechanically weak structural layers of IC pad introduced in low-k wafers will increase the pad crack possibilities.
- Now TSMC keeps practicing the SDMF as the standard guideline for monitoring and controlling the probing scrub marks in achieving the robust wafer sort.
- SDMF results can also be further implemented into probe card design in order to obtain acceptable probe depth.
- SDMF was again validated experimentally under consideration of more complete practical probing parameters. However, prober set-up (particularly chuck movement) still considered as important factor.
- Available BCF metrology is recently at its bottleneck limit, for low-k card, new enhancement tooling to obtaining accurate measurement is under request.



**Q & A**